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4V Drive Nch MOSFET

RSD080N06

● Structure

Silicon N-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) 4V drive.
- 3) High power package(CPT3).

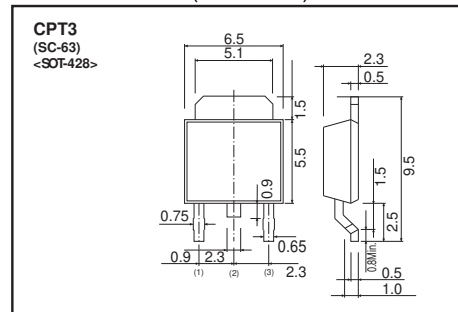
● Application

Switching

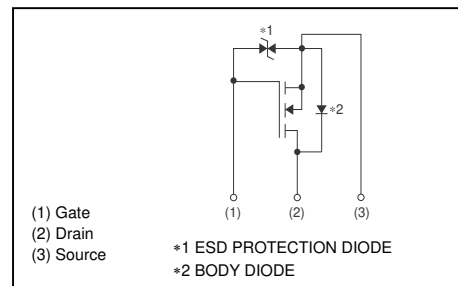
● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
RSD080N06		○

● Dimensions (Unit : mm)



● Inner circuit



● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	V_{DSS}	60	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	Continuous	I_D	± 8 A
	Pulsed	I_{DP} *1	± 16 A
Source current (Body Diode)	Continuous	I_S	8 A
	Pulsed	I_{SP} *1	16 A
Power dissipation	P_D *2	15	W
Channel temperature	T_{ch}	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$

*2 $T_C = 25^\circ C$

● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th(ch-c)}$ *	8.33	°C / W

* $T_C = 25^\circ C$

● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	± 10	μA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=60V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	57	80	m Ω	$I_D=8A, V_{GS}=10V$
		-	70	98		$I_D=8A, V_{GS}=4.5V$
		-	78	109		$I_D=8A, V_{GS}=4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	4.8	-	-	S	$V_{DS}=10V, I_D=8A$
Input capacitance	C_{iss}	-	380	-	pF	$V_{DS}=10V$
Output capacitance	C_{oss}	-	90	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	-	50	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	9	-	ns	$V_{DD}=30V, I_D=4A$
Rise time	t_r^*	-	13	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	30	-	ns	$R_L=7.5\Omega$
Fall time	t_f^*	-	10	-	ns	$R_G=10\Omega$
Total gate charge	Q_g^*	-	9.4	-	nC	$V_{DD}=30V, I_D=8A$
Gate-source charge	Q_{gs}^*	-	1.8	-	nC	$V_{GS}=10V$
Gate-drain charge	Q_{gd}^*	-	2.3	-	nC	

*Pulsed

● Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^*	-	-	1.5	V	$I_s=8A, V_{GS}=0V$

*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics (I)

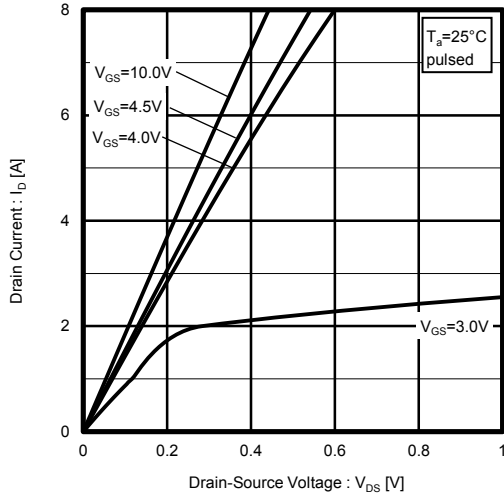


Fig.2 Typical Output Characteristics (II)

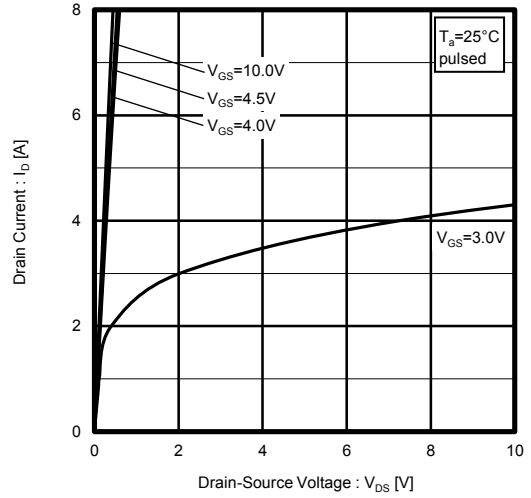


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

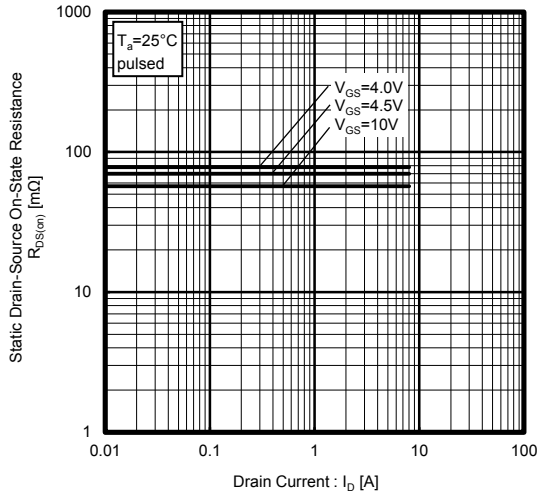


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

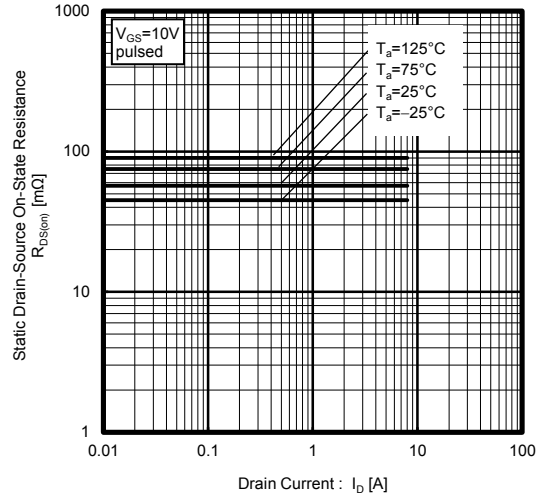


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

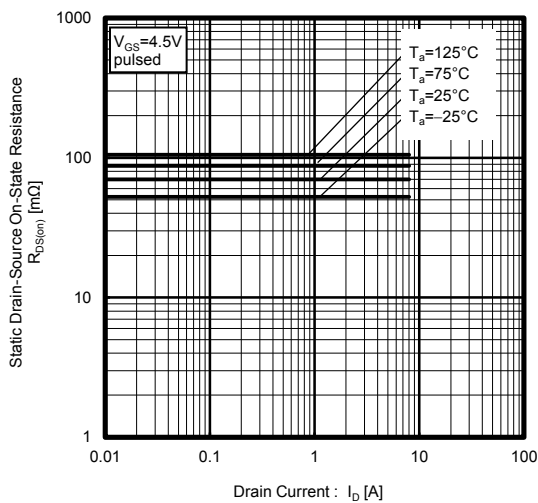


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

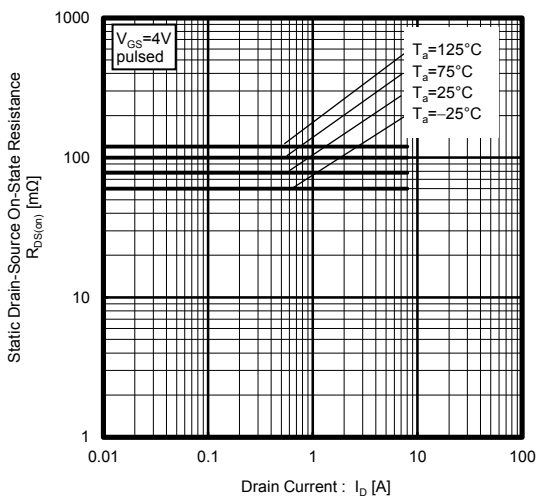


Fig.7 Forward Transfer Admittance vs. Drain Current

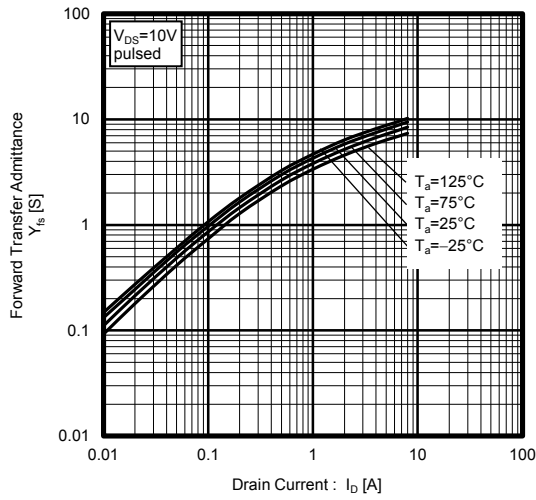


Fig.8 Typical Transfer Characteristics

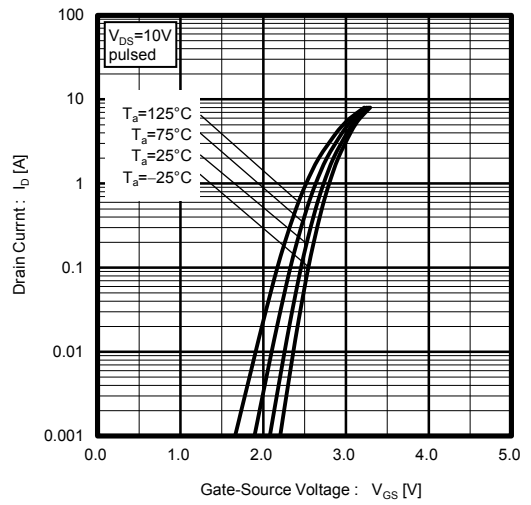


Fig.9 Source Current vs. Source-Drain Voltage

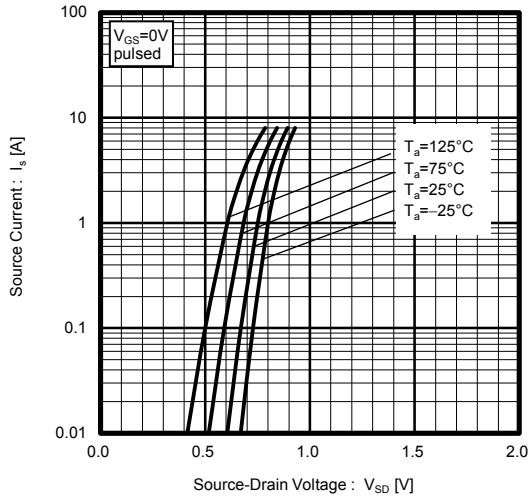


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

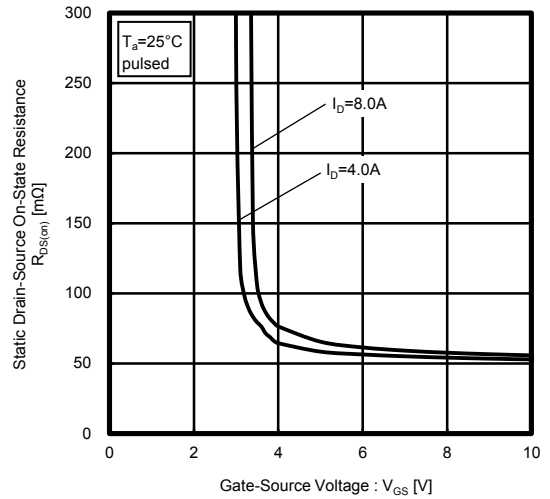


Fig.11 Switching Characteristics

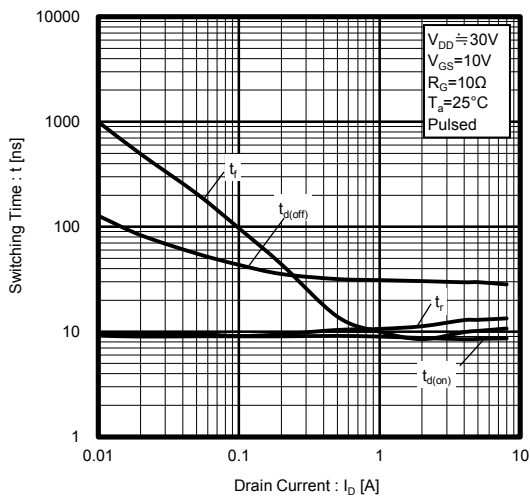


Fig.12 Dynamic Input Characteristics

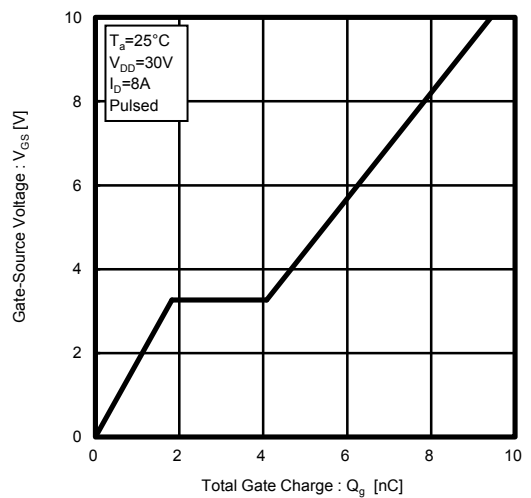


Fig.13 Typical Capacitance vs. Drain-Source Voltage

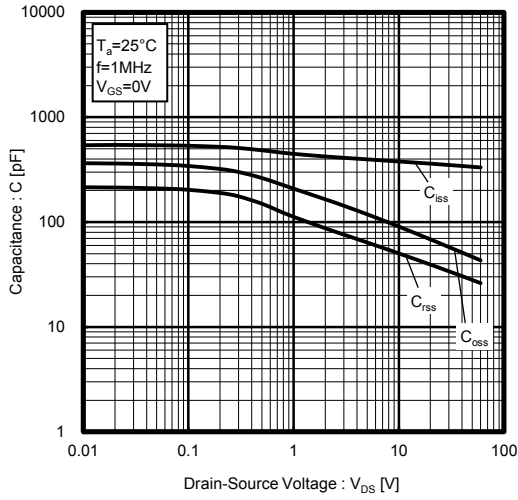


Fig.14 Maximum Safe Operating Area

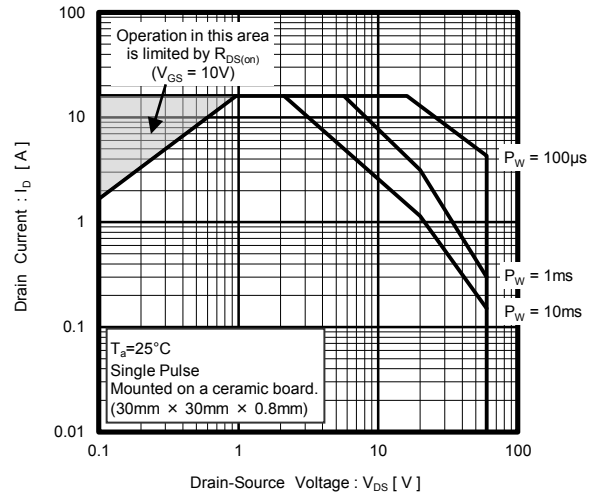
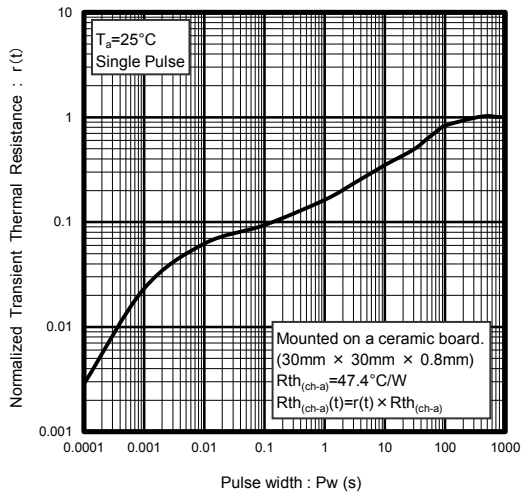


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



● Measurement circuits

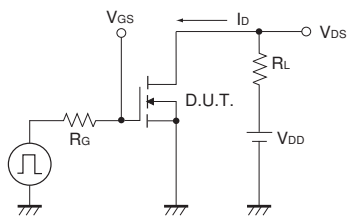


Fig.1-1 Switching Time Measurement Circuit

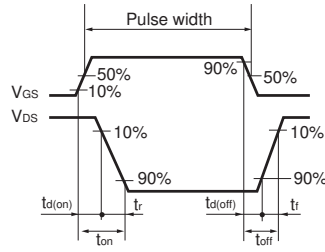


Fig.1-2 Switching Waveforms

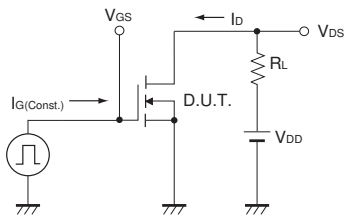


Fig.2-1 Gate Charge Measurement Circuit

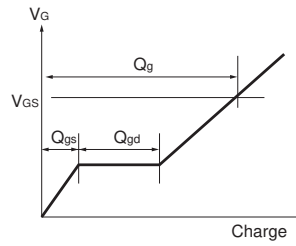


Fig.2-2 Gate Charge Waveform

Notes

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